

STUDY OF THE INFLUENCE
OF A HIGH TEMPERATURE
TREATMENT ON THE DISPERSION OF X-RAYS
BY DEFECTS GENERATED IN CRYSTALS Cz-Si

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S u m m a r y

By triple-crystal diffractometry, we study the dispersion of X-rays by Czochralski-grown silicon crystals with local defects appeared in them during the annealing at temperatures of 850–1000 °C and the repeated annealing at 1050 °C. The characteristics of admixture-structural complexes are calculated. A method of calculation of the radii and densities of clusters and dislocation loops and a method of diagnostics of the defects' type are proposed.